

Title (en)  
NISI SPUTTERING TARGET WITH IMPROVED GRAIN STRUCTURE

Title (de)  
NISI-SPUTTERTARGET MIT VERBESSERTER KORNSTRUKTUR

Title (fr)  
CIBLE DE PULVÉRISATION NISI À STRUCTURE DE GRAIN AMÉLIORÉE

Publication  
**EP 3757248 A1 20201230 (EN)**

Application  
**EP 19182532 A 20190626**

Priority  
EP 19182532 A 20190626

Abstract (en)  
The present invention relates to a sputtering target comprising a NiSi alloy comprising from 2 to 8 weight% Si, and to a process for forming said sputtering target.

IPC 8 full level  
**C23C 14/14** (2006.01); **C22C 19/03** (2006.01); **C23C 14/34** (2006.01); **H01J 37/34** (2006.01)

CPC (source: EP)  
**C22C 19/007** (2013.01); **C22C 19/03** (2013.01); **C23C 14/14** (2013.01); **C23C 14/3414** (2013.01); **H01J 37/3426** (2013.01); **H01J 37/3491** (2013.01)

Citation (applicant)  
• US 2008138974 A1 20080612 - LI YANPING [US], et al  
• US 6780295 B2 20040824 - IVANOV EUGENE Y [US]

Citation (search report)  
• [A] US 2006118407 A1 20060608 - IVANOV EUGENE Y [US]  
• [AD] US 6780295 B2 20040824 - IVANOV EUGENE Y [US]  
• [T] SPIEKERMANN P: "Legierungen - ein besonderes patentrechtliches Problem?", MITTEILUNGEN DER DEUTSCHEN PATENTANWAELTE, HEYMANN, KOLN, DE, vol. 34, 1 January 1993 (1993-01-01), pages 178 - 190, XP002152326, ISSN: 0026-6884

Designated contracting state (EPC)  
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)  
BA ME

DOCDB simple family (publication)  
**EP 3757248 A1 20201230**; **EP 3757248 B1 20220413**; MY 195195 A 20230111; WO 2020260094 A1 20201230

DOCDB simple family (application)  
**EP 19182532 A 20190626**; EP 2020066782 W 20200617; MY PI2021007065 A 20200617